



## N-Channel 60-V (D-S), 175°C MOSFET, Logic Level

## PRODUCT SUMMARY

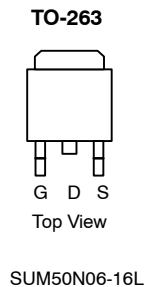
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
60	0.016 @ $V_{GS} = 10$ V	50
	0.022 @ $V_{GS} = 4.5$ V	43

## FEATURES

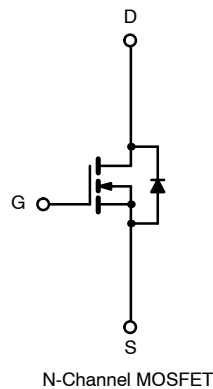
- TrenchFET® Power MOSFET
- 175°C Junction Temperature

## APPLICATIONS

- 12-V Automotive Systems
  - Load Switch
  - Motor Drive
  - DC/DC



DRAIN connected to TAB

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	60	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 175^\circ\text{C}$ )	$T_C = 25^\circ\text{C}$	$I_D$	50	A
	$T_C = 100^\circ\text{C}$		35	
Pulsed Drain Current		$I_{DM}$	100	
Avalanche Current		$I_{AR}$	40	
Repetitive Avalanche Energy <sup>a</sup>	$L = 0.1$ mH	$E_{AR}$	80	mJ
Power Dissipation	$T_C = 25^\circ\text{C}$	$P_D$	93 <sup>b</sup>	W
	$T_A = 25^\circ\text{C}^c$		3.7 <sup>c</sup>	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 175	$^\circ\text{C}$

## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) <sup>c</sup>	$R_{thJA}$	40	$^\circ\text{C/W}$
Junction-to-Case	$R_{thJC}$	1.6	

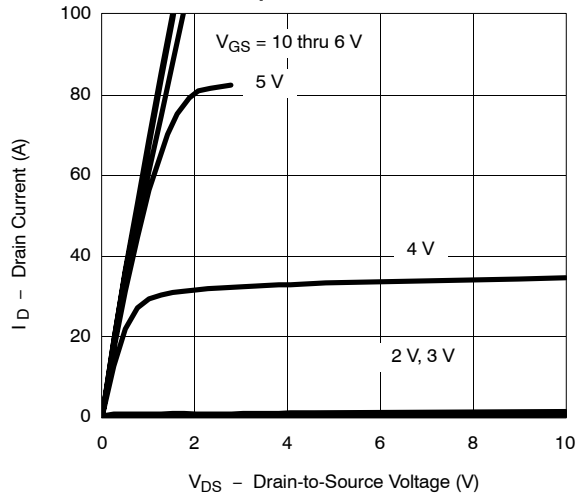
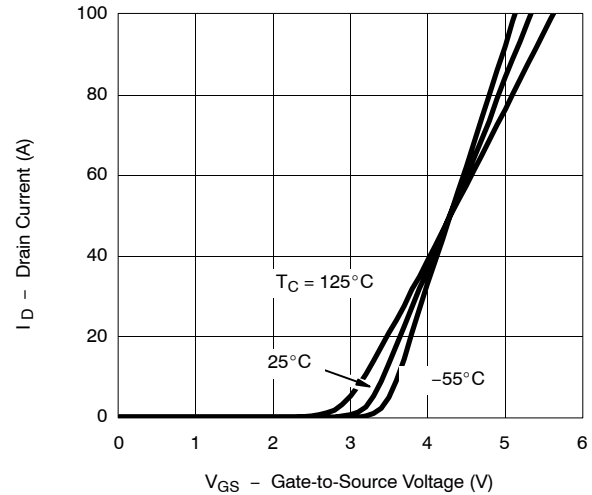
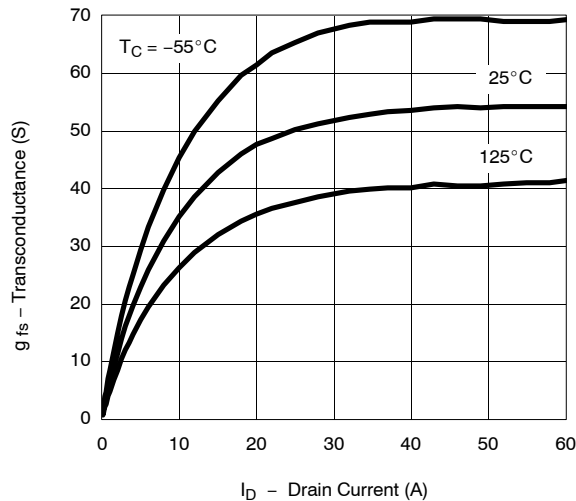
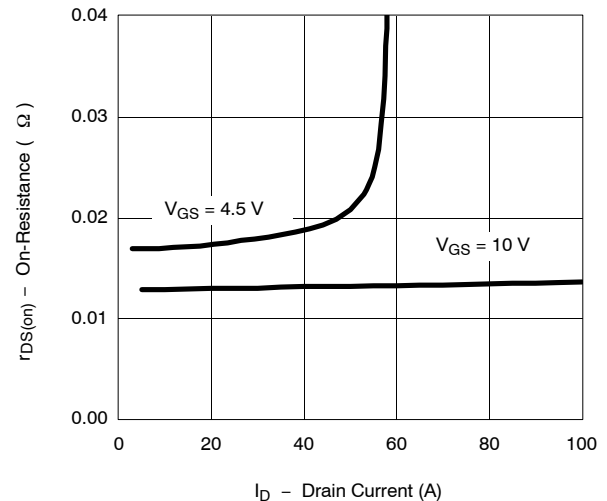
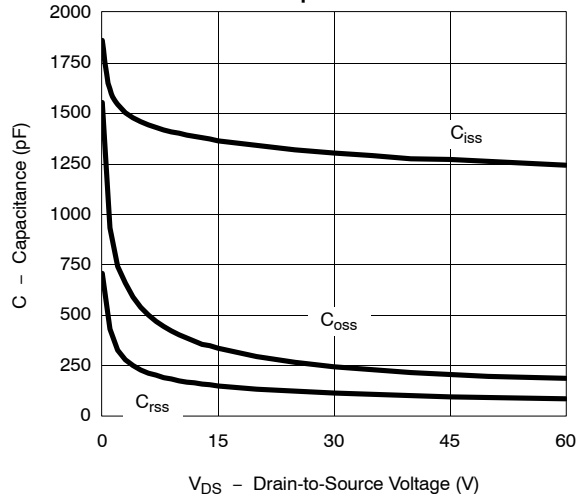
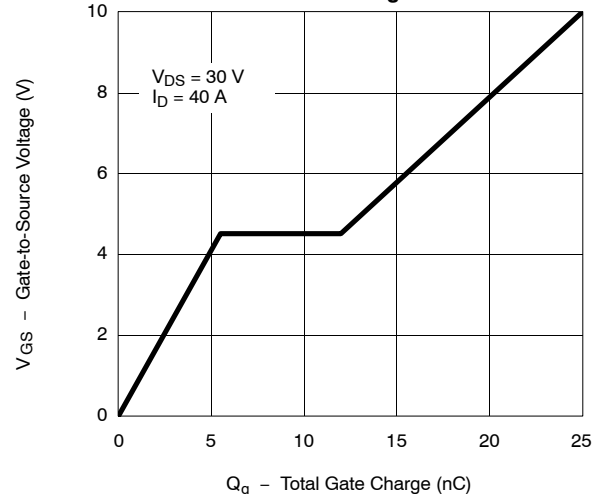
## Notes:

- Duty cycle  $\leq 1\%$ .
- See SOA curve for voltage derating.
- Surface Mounted on FR4 Board,  $t \leq 10$  sec.

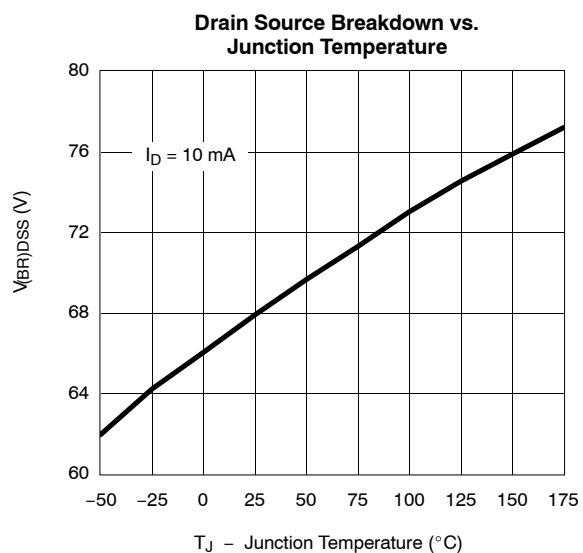
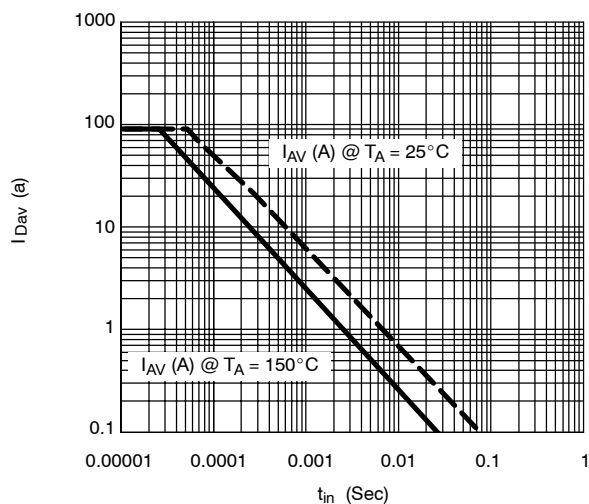
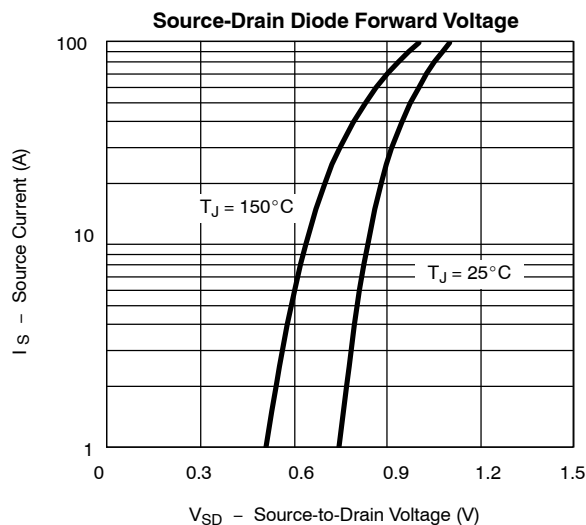
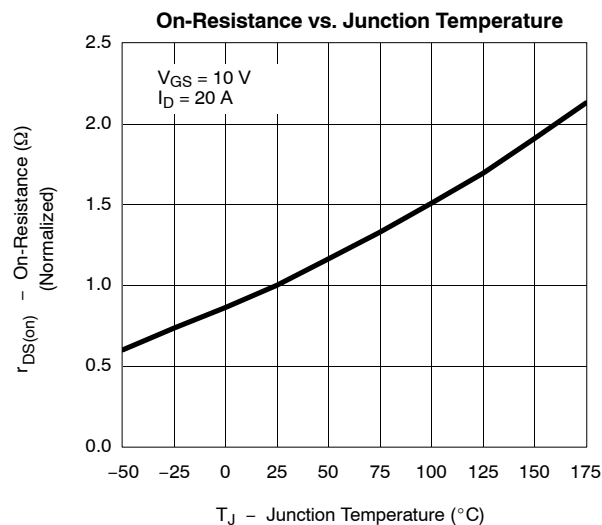
SPECIFICATIONS (T <sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	60			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>DS</sub> = 250 μA	1.0	2.0	3.0	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	50			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.013	0.016	Ω
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C			0.028	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C			0.036	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A		0.017	0.022	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		50		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		1325		pF
Output Capacitance	C <sub>oss</sub>			265		
Reverse Transfer Capacitance	C <sub>rss</sub>			115		
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 50 A		25	40	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			5.5		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			6.5		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 30 V, R <sub>L</sub> = 0.8 Ω I <sub>D</sub> ≈ 50 A, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 2.5 Ω		10	20	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			9	20	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			25	50	
Fall Time <sup>c</sup>	t <sub>f</sub>			7	15	
Source-Drain Diode Ratings and Characteristics (T <sub>C</sub> = 25 °C) <sup>b</sup>						
Continuous Current	I <sub>s</sub>				50	A
Pulsed Current	I <sub>SM</sub>				100	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 50 A, V <sub>GS</sub> = 0 V		1.0	1.5	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 50 A, di/dt = 100 A/μs		35	70	ns
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>			2.3	4	A
Reverse Recovery Charge	Q <sub>rr</sub>				0.04	0.14

## Notes:

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.  
c. Independent of operating temperature.

**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)****Output Characteristics****Transfer Characteristics****Transconductance****On-Resistance vs. Drain Current****Capacitance****Gate Charge**

### TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)





**THERMAL RATINGS**

